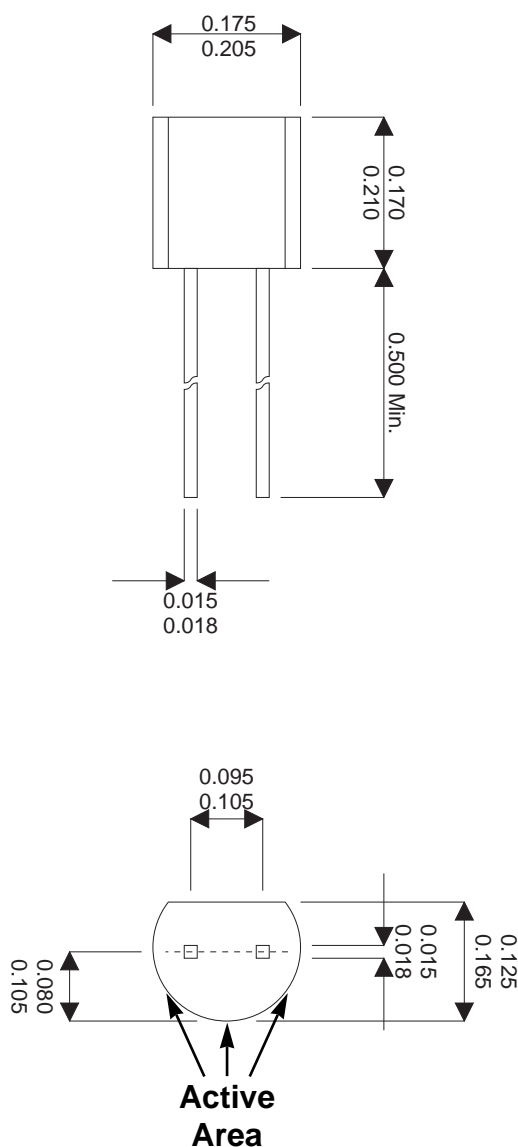


## MECHANICAL DATA

Dimensions in inches.



**TO-92 Package**

## P.I.N. PHOTODIODE



## FEATURES

- RED PLASTIC ENCAPSULATED PACKAGE
- 0.1" (2.54mm) LEAD SPACING
- BUILT IN FILTER
- SUITABLE FOR REMOTE CONTROL
- LOW DARK CURRENT

## DESCRIPTION

The SMP400G-X4 is a silicon PIN photodiode which is incorporated in a red plastic package which simultaneously serves as a filter and is also transparent for the red to infra-red emission. The terminals are solder tabs with 0.1" (2.54mm) spacing. Due to its design the diode can be assembled vertically on PC board.

Arrays can be realised by multiple arrangements. This versatile photo detector can be used as a diode as well as a voltage cell.

The PIN photodiode is outstanding for low junction capacitance, high cut off frequency and short switching time. It is particularly suitable for IR sound transmission and remote control.

## ABSOLUTE MAXIMUM RATINGS (T<sub>case</sub> = 25°C unless otherwise stated)

Operating temperature range	-40°C to +70°C
Storage temperature range	-45°C to +80°C
Temperature coefficient of responsivity	0.35% per °C
Temperature coefficient of dark current	x2 per 8°C rise
Reverse Breakdown Voltage	60V

**CHARACTERISTICS** (T<sub>amb</sub>=25°C unless otherwise stated)

Characteristic	Test Conditions.	Min.	Typ.	Max.	Units
Responsively	λ at 900nm	0.45	0.55		A/W
Active Area			0.62		mm <sup>2</sup>
Dark Current	E = 0 Dark    1V Reverse		0.1	1.0	nA
	E = 0 Dark    10V Reverse		0.5	2.5	
Breakdown Voltage	E = 0 Dark    10μA Reverse	60	80		V
Capacitance	E = 0 Dark    0V Reverse		8	12	pF
	E = 0 Dark    20V Reverse		1.5	2.5	
Rise Time	30V Reverse 50Ω		4		ns
NEP	900nm		7.2		W/√Hz

